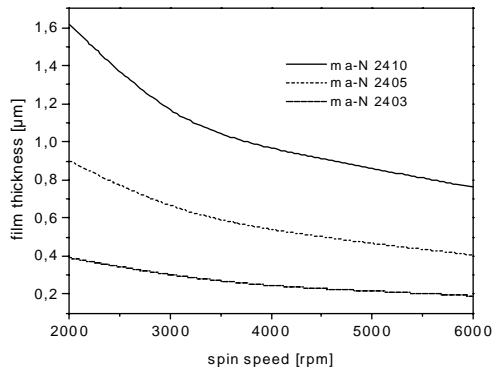


Product Information Negative Tone Photoresist ma-N 2400

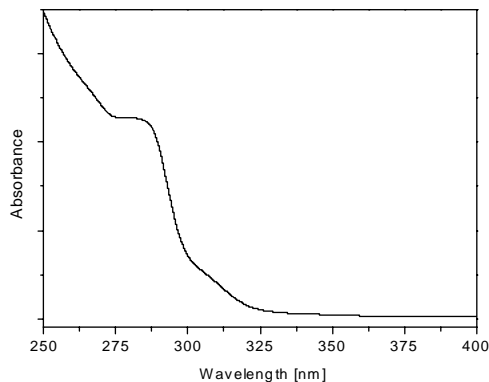
The **ma-N 2400** series is an innovation in negative tone photoresists for flexible use in conventional photolithography as well as e-beam lithography. Full application compatibility to processing of conventional positive tone photoresists is guaranteed.

Thickness Range



ma-N 2400 is processed by spin coating, spraying or dipping. Film thicknesses from 0.2 - 1.6 µm can be obtained depending on the solid content of the resist solution and the spinning speed.

Spectral Sensitivity



UV-VIS absorbance of **ma-N 2400**

The **ma-N 2400** series can be used successfully in e-beam lithography.

Processing

Processing of **ma-N 2400** is fully compatible to positive tone photoresists. During the development in aqueous-alkaline or metal ion free developer the structures do not swell.

Deposition Stability

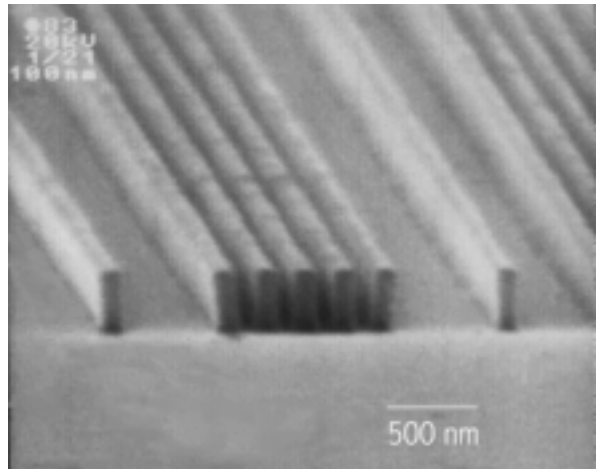
The excellent etch resistance in plasma processes as well as in acidic and alkaline solutions make **ma-N 2400** the best choice for etch masks. The **ma-N 2400** series is well suited for electrodeposition.

Stripping

The chemical composition of **ma-N 2400** allows easy and residue-free resist removal.

Pattern Transfer

Depending on the film thickness, a resolution to 0.2 µm is possible using e-beam.



Single line/lines & spaces of 100 nm (on the left) and of 90 nm (on the right) width film thickness 0.35 µm, exposure dose 101 µC/cm² (LION LV1, 20 kV), developer MIF 726, 30 sec

Environmental and Health Protection

All harmful organic solvents in resist and developer were substituted and are based on safe solvents.